



P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A)
-20	0.065 @ V _{GS} = -4.5 V	-4.9
	0.095 @ V _{GS} = -2.5 V	-4.1

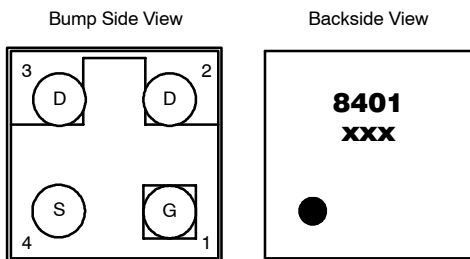
FEATURES

- TrenchFET® Power MOSFET
- New MICRO FOOT® Chipscale Packaging Reduces Footprint Area Profile (0.62 mm) and On-Resistance Per Footprint Area
- Pin Compatible to Industry Standard Si3443DV

APPLICATIONS

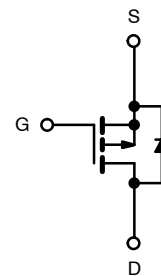
- PA, Battery and Load Switch
- Battery Charger Switch
- PA Switch

MICRO FOOT



Device Marking: 8401
xxx = Date/Lot Traceability Code

Ordering Information: Si8401DB-T1
Si8401DB-T1—E1 (Lead (Pb)-Free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)					
Parameter	Symbol	5 secs	Steady State	Unit	
Drain-Source Voltage	V _{DS}	-20		V	
Gate-Source Voltage	V _{GS}	± 12			
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	-4.9	-3.6	A
		T _A = 70 °C	-3.9	-2.8	
Pulsed Drain Current	I _{DM}	-10			
continuous Source Current (Diode Conduction) ^a	I _S	-2.5	-2.5		
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	2.77	1.47	W
		T _A = 70 °C	1.77	0.94	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150		°C
Package Reflow Conditions ^b	VPR	215/245°			
	IR/Convection	220/250°			

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R _{thJA}	t ≤ 5 sec	35	45	°C/W
		Steady State	72	85	
Maximum Junction-to-Foot (drain)	R _{thJF}	16	20		

Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Refer to IPC/JEDEC (J-STD-020A), no manual or hand soldering.
- Package reflow conditions for lead-free.

SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)

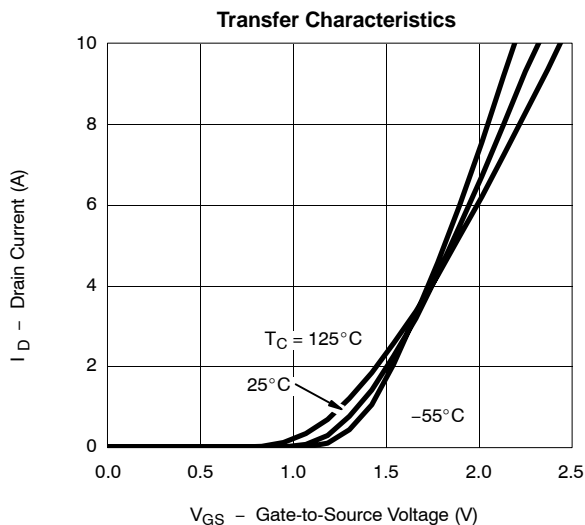
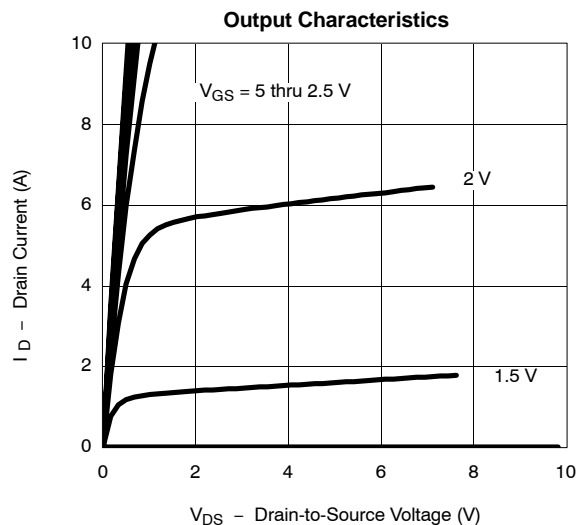
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-0.45	-0.9	1.4	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±12 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -20 V, V _{GS} = 0 V			-1	μA
		V _{DS} = -20 V, V _{GS} = 0 V, T _J = 70 °C			-5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≤ -5 V, V _{GS} = -4.5 V	-5			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = -4.5 V, I _D = -1 A		0.057	0.065	Ω
		V _{GS} = -2.5 V, I _D = -1 A		0.080	0.095	
Forward Transconductance ^a	g _{fs}	V _{DS} = -10 V, I _D = -1 A		6		S
Diode Forward Voltage ^a	V _{SD}	I _S = -1 A, V _{GS} = 0 V		-0.73	-1.1	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = -10 V, V _{GS} = -4.5 V, I _D = -1 A		11	17	nC
Gate-Source Charge	Q _{gs}			2.1		
Gate-Drain Charge	Q _{gd}			2.9		
Turn-On Delay Time	t _{d(on)}	V _{DD} = -10 V, R _L = 10 Ω I _D ≅ -1 A, V _{GEN} = -4.5 V, R _G = 6 Ω		17	25	ns
Rise Time	t _r			28	45	
Turn-Off Delay Time	t _{d(off)}			88	135	
Fall Time	t _f			60	90	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = -1 A, di/dt = 100 A/μs		40	60	ns
Reverse Recovery Charge	Q _{rr}			20	30	

Notes

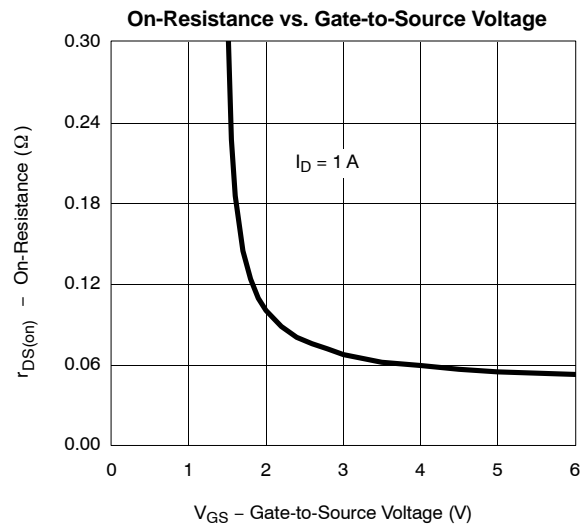
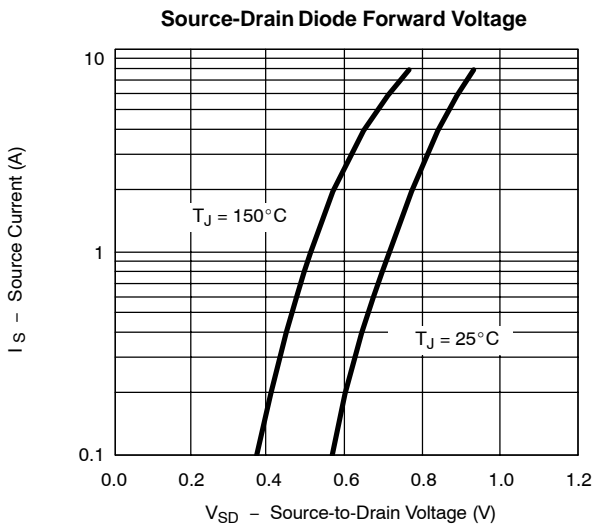
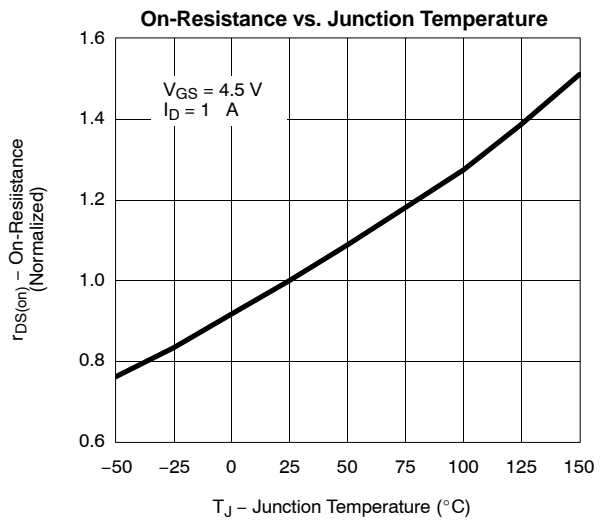
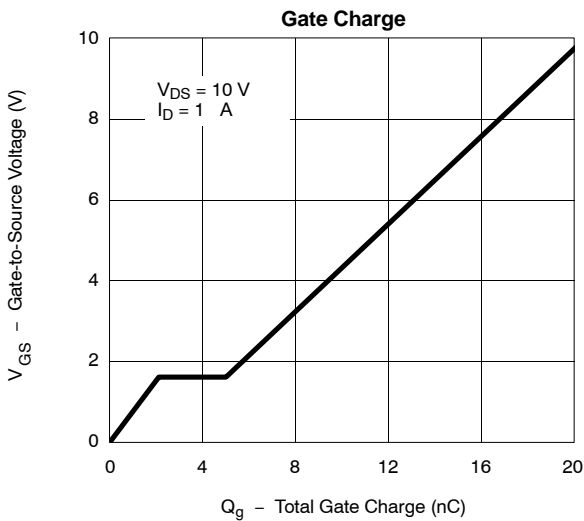
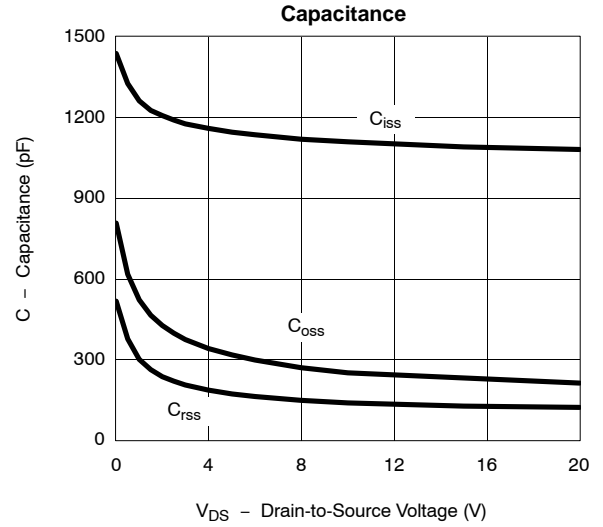
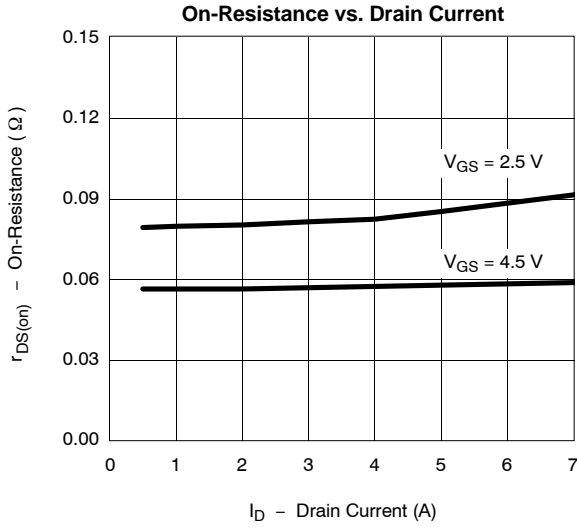
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

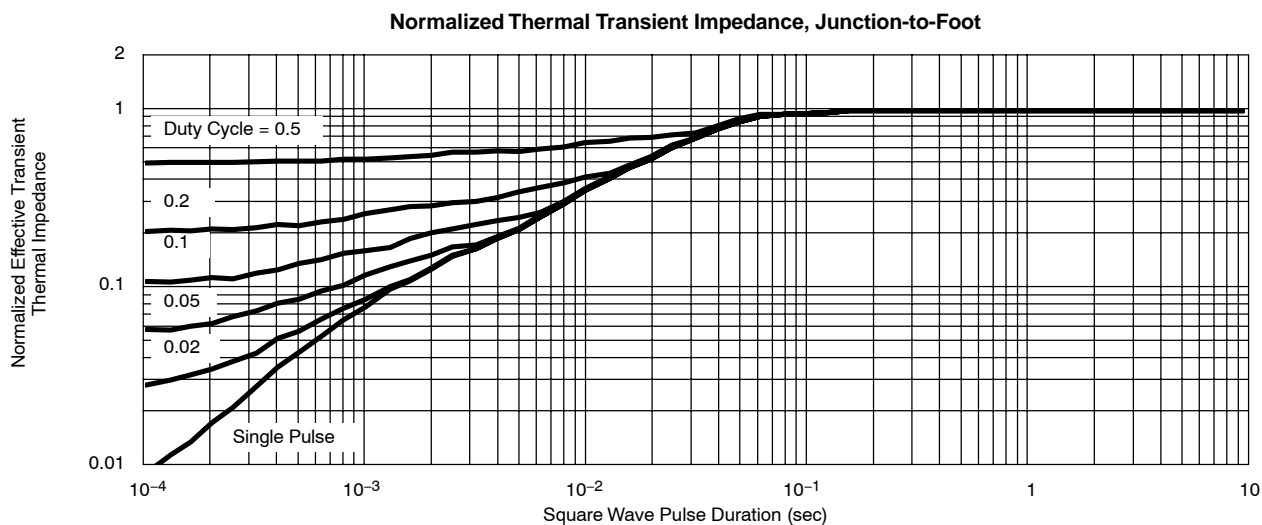
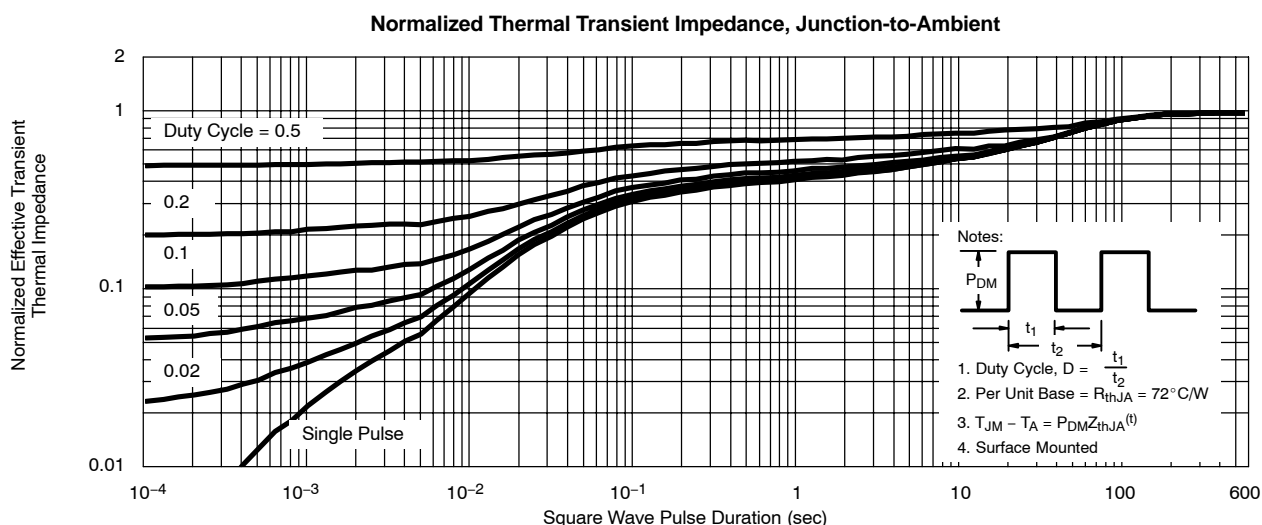
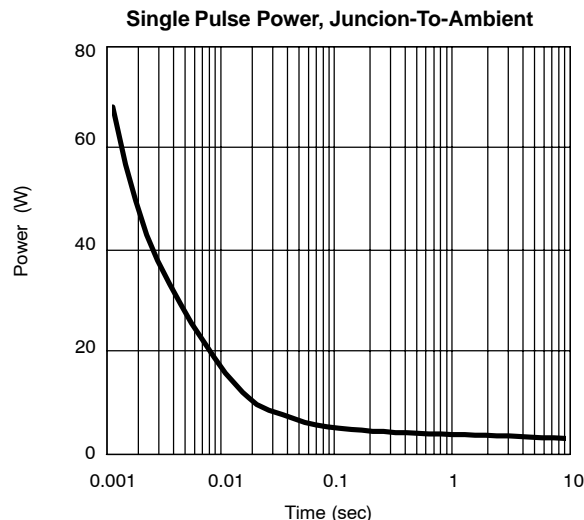
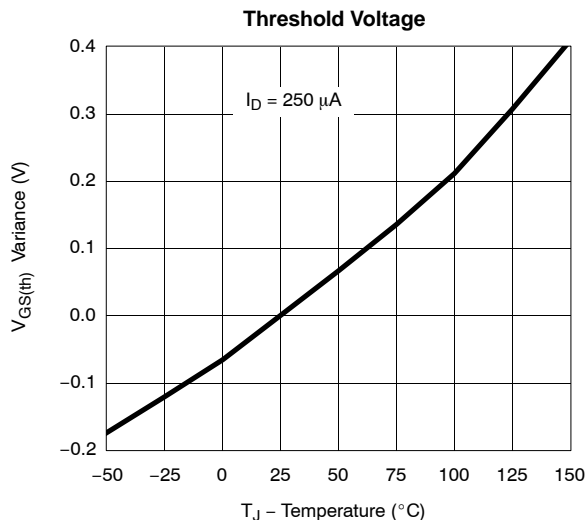
TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)



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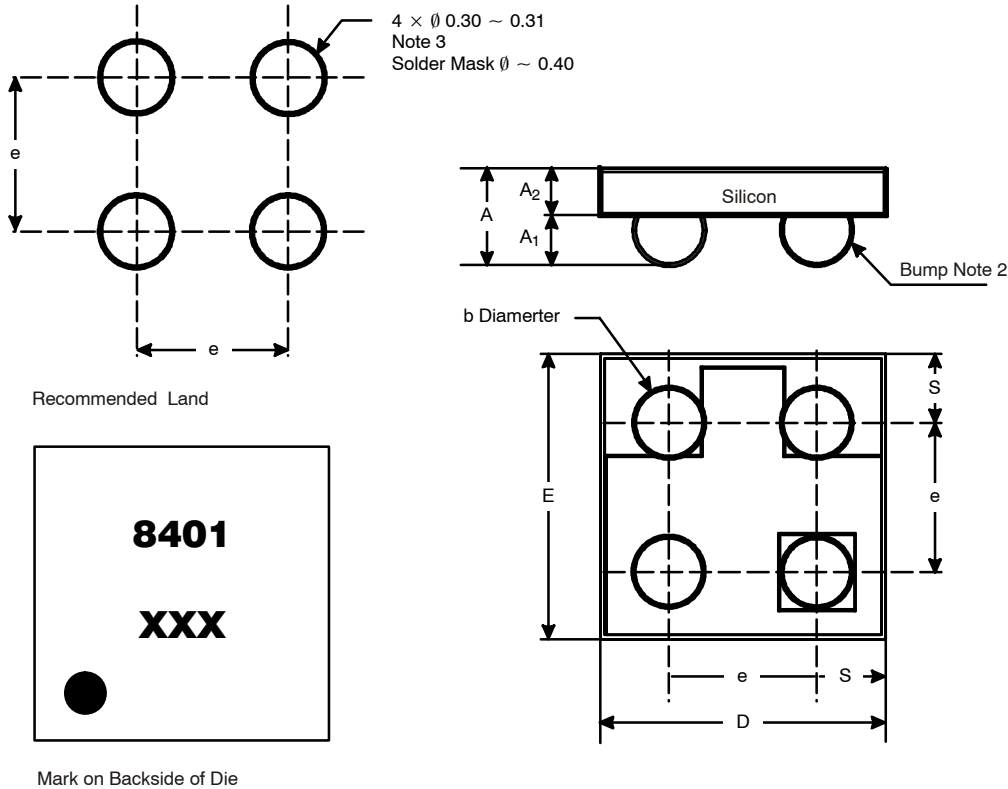


TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)



PACKAGE OUTLINE

MICRO FOOT: 4-BUMP (2 X 2, 0.8-mm PITCH)



NOTES (Unless Otherwise Specified):

1. Laser mark on the silicon die back, coated with a thin metal.
2. Bumps are Eutectic solder 63/57 Sn/Pb. (Sn 3.8 Ag, 0.7 Cu for Pb-free bumps)
3. Non-solder mask defined copper landing pad.
4. The flat side of wafers is oriented at the bottom.

Dim	MILLIMETERS*		INCHES	
	Min	Max	Min	Max
A	0.600	0.650	0.0236	0.0256
A ₁	0.260	0.290	0.0102	0.0114
A ₂	0.340	0.360	0.0134	0.0142
b	0.370	0.410	0.0146	0.0161
D	1.520	1.600	0.0598	0.0630
E	1.520	1.600	0.0598	0.0630
e	0.750	0.850	0.0295	0.0335
S	0.370	0.380	0.0146	0.0150

* Use millimeters as the primary measurement.

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